| L Number | Hits | Search Text | DB | Time stamp |
|-------------|------|--|--|---------------------|
| 2 | 2172 | (semiconductor adj3 memory) same (cell\$2 adj3 block\$2) | USPAT; US-PGPUB; EPO; JPO; DERWENT; | 2004/10/18 03:01 |
| 3 | 107 | ((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) same (stor\$2 adj3 data) | IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/10/18 |
| 4 | 8 | (((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) same (stor\$2 adj3 data)) same redundancy | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/10/18 03:00 |
| 5 | 38 | (cell adj3 block) same (stor\$3 adj3 data) same redundancy | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/10/18 03:01 |
| 6 | 6 | ((cell adj3 block) same (stor\$3 adj3 data) same redundancy) and ECC | USPAT; US-PGPUB; EPO; JPO; DERWENT; | 2004/10/18 03:01 |
| 7 | 378 | ((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls. | IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/10/18 03:01 |
| 8 | 4 | (((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.) and redundancy and ECc | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/10/18 03:02 |
| 9 | 14 | choi-sung-h.in. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/10/18 |
| 10 | 433 | choi-sung-\$.in. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/10/18 |
| 11 | 2 | choi-sung.in. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/10/18 |
| 12 | 0 | (((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.) and ECC and repair | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/10/18 |
| 13 | 118 | (((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.) and repair | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/10/18 03:04 |
| 14 | 94 | ((((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.) and repair) and redundanc\$3 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/10/18 |

| 15 | 94 | (((((semiconductor adj3 memory) same | USPAT; | 2004/10/18 |
|----|----|--|-----------|------------|
| | | (cell\$2 adj3 block\$2)) and | US-PGPUB; | 03:04 |
| l | | 365/200,201,225.7.ccls.) and repair) and | EPO; JPO; | |
| | | redundanc\$3) and 365/\$7.ccls. | DERWENT; | |
| | | | IBM TDB | |
| 16 | 94 | ((((semiconductor adj3 memory) same | USPAT; | 2004/10/18 |
| İ | | (cell\$2 adj3 block\$2)) and | US-PGPUB; | 03:04 |
| ļ | | 365/200,201,225.7.ccls.) and repair) and | EPO; JPO; | |
| | | redundanc\$3) and ((semiconductor adj3 | DERWENT; | |
| | | memory) same (cell\$2 adj3 block\$2)) | IBM TDB | |
| 17 | 3 | | USPĀT; | 2004/10/18 |
| | | (cell\$2 adj3 block\$2)) and | US-PGPUB; | 03:05 |
| i | | 365/200,201,225.7.ccls.) and repair) and | EPO; JPO; | |
| 1 | | redundanc\$3) and (((semiconductor adj3 | DERWENT; | |
| | | memory) same (cell\$2 adj3 block\$2)) same | IBM TDB | |
| | | (stor\$2 adj3 data)) | | |
| 18 | 12 | ((cell adj3 block) same (stor\$3 adj3 | USPAT; | 2004/10/18 |
| 10 | | data) same redundancy) and | US-PGPUB; | 03:05 |
| | | (((semiconductor adj3 memory) same | EPO; JPO; | "" |
| | | (cell\$2 adj3 block\$2)) and | DERWENT; | |
| | | 365/200,201,225.7.ccls.) | IBM TDB | |
| 19 | 8 | | USPAT; | 2004/10/18 |
| 19 | | data) same redundancy) and | US-PGPUB; | 03:05 |
| | | | EPO; JPO; | 05.05 |
| | | (((semiconductor adj3 memory) same | DERWENT; | |
| | | (cell\$2 adj3 block\$2)) and | | |
| | | 365/200,201,225.7.ccls.)) and | IBM_TDB | 1 |
| | | ((((((semiconductor adj3 memory) same | | |
| | | (cell\$2 adj3 block\$2)) and | | |
| | | 365/200,201,225.7.ccls.) and repair) and | | |
| | | redundanc\$3) and 365/\$7.ccls.) | L | |